

L Number	Hits	Search Text	DB	Time stamp
1	10556	ldd\$1	USPAT; US-PGPUB	2004/04/22 19:45
2	8557	lightly adj doped adj2 drain	USPAT; US-PGPUB	2004/04/22 19:45
3	270457	resistor\$1	USPAT; US-PGPUB	2004/04/22 19:45
4	7676	spacer\$1 near2 remov\$3	USPAT; US-PGPUB	2004/04/22 19:48
5	152	(ldd\$1 or (lightly adj doped adj2 drain)) and resistor\$1 and (spacer\$1 near2 remov\$3)	USPAT; US-PGPUB	2004/04/22 19:48
18	204	electrostatic adj discharge adj device	USPAT; US-PGPUB	2004/04/22 20:09
19	6929	ESD	USPAT; US-PGPUB	2004/04/22 20:09
20	2973	resistor\$1 and ((electrostatic adj discharge adj device) or ESD)	USPAT; US-PGPUB	2004/04/22 20:09
21	77049	438/\$.ccls.	USPAT; US-PGPUB	2004/04/22 20:10
22	143248	257/\$.ccls.	USPAT; US-PGPUB	2004/04/22 20:11
23	209764	spacer\$1	USPAT; US-PGPUB	2004/04/22 20:11
24	170475	sidewall\$1	USPAT; US-PGPUB	2004/04/22 20:11
25	346332	side adj wall\$1	USPAT; US-PGPUB	2004/04/22 20:11
26	82010	(spacer\$1 or sidewall\$1 or (side adj wall\$1)) same remove\$3	USPAT; US-PGPUB	2004/04/22 20:18
27	117	(resistor\$1 and ((electrostatic adj discharge adj device) or ESD)) and (438/\$.ccls. or 257/\$.ccls.) and ((spacer\$1 or sidewall\$1 or (side adj wall\$1)) same remove\$3)	USPAT; US-PGPUB	2004/04/22 20:19
28	105771	(spacer\$1 or sidewall\$1 or (side adj wall\$1)) same remov\$3	USPAT; US-PGPUB	2004/04/22 20:18
29	141	(resistor\$1 and ((electrostatic adj discharge adj device) or ESD)) and (438/\$.ccls. or 257/\$.ccls.) and ((spacer\$1 or sidewall\$1 or (side adj wall\$1)) same remov\$3)	USPAT; US-PGPUB	2004/04/22 20:19

L Number	Hits	Search Text	DB	Time stamp
5	209764	spacer\$1	USPAT; US-PGPUB	2004/04/22 16:15
6	170475	sidewall\$1	USPAT; US-PGPUB	2004/04/22 16:16
7	346332	side adj wall\$1	USPAT; US-PGPUB	2004/04/22 16:16
8	2011799	remov\$3	USPAT; US-PGPUB	2004/04/22 16:16
9	66033	field adj effect adj transistor\$1	USPAT; US-PGPUB	2004/04/22 16:16
10	44108	\$1MOS adj transistor	USPAT; US-PGPUB	2004/04/22 16:17
11	2553	igfet\$1	USPAT; US-PGPUB	2004/04/22 16:17
12	2275	misfet\$1	USPAT; US-PGPUB	2004/04/22 16:20
13	42296	m\$1sfet\$1	USPAT; US-PGPUB	2004/04/22 16:21
14	1762	nm\$1sfet\$1	USPAT; US-PGPUB	2004/04/22 16:21
15	1593	pm\$1sfet\$1	USPAT; US-PGPUB	2004/04/22 16:21
16	17402	nmos adj transistor\$1	USPAT; US-PGPUB	2004/04/22 16:22
17	15673	pmos adj transistor\$1	USPAT; US-PGPUB	2004/04/22 16:22
18	48508	\$1fet	USPAT; US-PGPUB	2004/04/22 16:23
19	447	resistor\$1 and (((field adj effect adj transistor\$1) or (\$1MOS adj transistor) or igfet\$1 or misfet\$1 or m\$1sfet\$1 or nm\$1sfet\$1 or pm\$1sfet\$1 or (nmos adj transistor\$1) or (pmos adj transistor\$1) or \$1fet) and ((spacer\$1 or sidewall\$1 or (side adj wall\$1)) near3 remov\$3)	USPAT; US-PGPUB	2004/04/22 16:34
26	204	electrostatic adj discharge adj device	USPAT; US-PGPUB	2004/04/22 18:55
27	6929	ESD	USPAT; US-PGPUB	2004/04/22 18:01
28	2973	resistor\$1 and ((electrostatic adj discharge adj device) or ESD)	USPAT; US-PGPUB	2004/04/22 18:02
29	77049	438/\$.ccls.	USPAT; US-PGPUB	2004/04/22 18:02
30	143248	257/\$.ccls.	USPAT; US-PGPUB	2004/04/22 18:02
31	1075	(resistor\$1 and ((electrostatic adj discharge adj device) or ESD)) and (438/\$.ccls. or 257/\$.ccls.)	USPAT; US-PGPUB	2004/04/22 18:03
32	141	((resistor\$1 and ((electrostatic adj discharge adj device) or ESD)) and (438/\$.ccls. or 257/\$.ccls.)) and ((spacer\$1 or sidewall\$1 or (side adj wall\$1)) same remov\$3)	USPAT; US-PGPUB	2004/04/22 18:53
35	8055	electro\$1static adj discharge	USPAT; US-PGPUB	2004/04/22 18:54
36	7676	spacer\$1 near2 remov\$3	USPAT; US-PGPUB	2004/04/22 18:55
37	20	(ESD or (electro\$1static adj discharge)) and resistor\$1 and (spacer\$1 near2 remov\$3)	USPAT; US-PGPUB	2004/04/22 18:56